ERRATA

Erratum: Effect of the diameter of the photoexcited region on the picosecond relaxation of bleaching in a thin layer of GaAs [Semiconductors 32, 484–487 (May 1998)]; Stimulated-emission spectrum arising from interband absorption of a picosecond optical pulse in a thin layer of GaAs [Semiconductors 32, 479–483 (May 1998)]

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Fiz. Tekh. Poluprovodn. **33**, 119 (January 1999)

[S1063-7826(99)02501-6]

On page 484, in the abstract, line 5 from the top should read “rate of superluminescence recombination.”

On page 484, left-hand column, line 2 of the second paragraph should read “intensity of superluminescent emission.”

On page 485, in Eq. (1), $\mu_e = \mu_h \approx E_g$ should read $\mu_e - \mu_h \approx E_g$.

On page 485, right-hand column, line 12 from the bottom should read “in Ref. 1.”

On page 480, right-hand column, line 15 from the bottom should read “when $F=0.2$ mm.”

Translated by M. E. Alferieff